CD74HC253, CD74HCT253

Data sheet acquired from Harris Semiconductor
SCHS170B

November 1997 - Revised October 2003

High-Speed CMOS Logic Dual 4-Input Multiplexer

Features

- **Common Select Inputs**
- **Separate Output-Enable Inputs**
- **Three-State Outputs**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55^{O}C to 125^{O}C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Description

The CD74HC253 and CD74HCT253 are dual 4-to-1 line selector/multiplexers having three-state outputs. One of four sources for each section is selected by the common select inputs, S0 and S1. When the output enable ($\overline{1OE}$, $\overline{2OE}$) is HIGH, the output is in the high-impedance state.

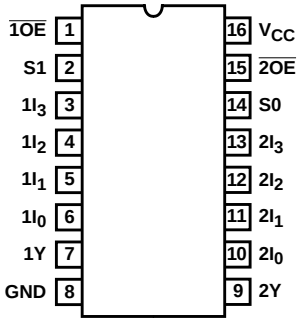
Ordering Information

PART NUMBER	TEMP. RANGE (^{O}C)	PACKAGE
CD74HC253E	-55 to 125	16 Ld PDIP
CD74HC253M	-55 to 125	16 Ld SOIC
CD74HC253MT	-55 to 125	16 Ld SOIC
CD74HC253M96	-55 to 125	16 Ld SOIC
CD74HCT253E	-55 to 125	16 Ld PDIP
CD74HCT253M	-55 to 125	16 Ld SOIC
CD74HCT253MT	-55 to 125	16 Ld SOIC
CD74HCT253M96	-55 to 125	16 Ld SOIC

NOTE: When ordering, use the entire part number. The suffix 96 denotes tape and reel. The suffix T denotes a small-quantity reel of 250.

Pinout

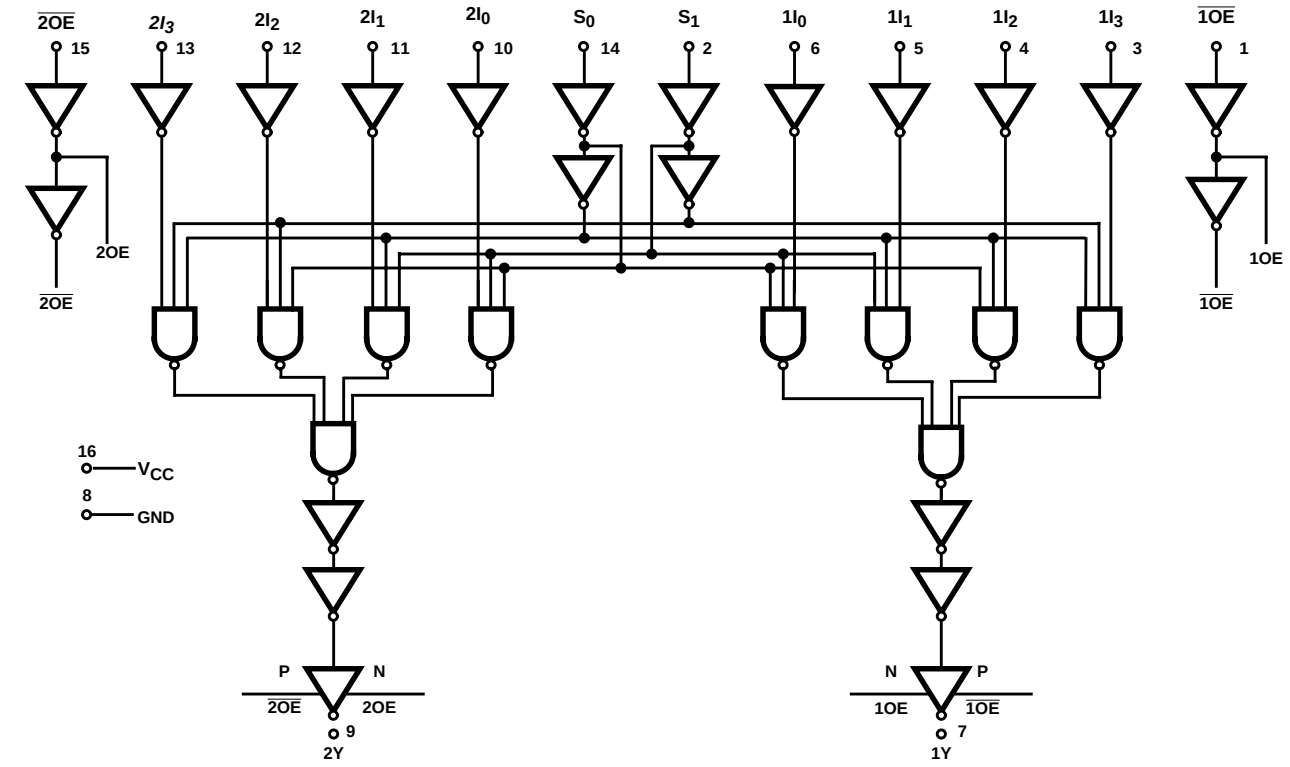
CD74HC253, CD74HCT253
(PDIP, SOIC)
TOP VIEW



CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

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Functional Diagrams



TRUTH TABLE

SELECT INPUTS (Note 1)		DATA INPUTS				OUTPUT ENABLE	OUTPUT
S1	S0	I_0	I_1	I_2	I_3	$\overline{OE}$	Y
X	X	X	X	X	X	H	Z
L	L	L	X	X	X	L	L
L	L	H	X	X	X	L	H
L	H	X	L	X	X	L	L
L	H	X	H	X	X	L	H
H	L	X	X	L	X	L	L
H	L	X	X	H	X	L	H
H	H	X	X	X	L	L	L
H	H	X	X	X	H	L	H

H = High Voltage Level, L = Low Voltage Level, X = Don't Care, Z = High Impedance (Off).
NOTE:

1. Select inputs S1 and S0 are common to both sections.

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Drain Current, per Output, I_O
For -0.5V < V_O < V_{CC} + 0.5V . . . . . ±35mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} . . . . . ±50mA

Operating Conditions

Temperature Range, T_A . . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 2)	θ_{JA} (°C/W)
E (PDIP) Package	67
M (SOIC) Package	73

Maximum Junction Temperature . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

2. The package thermal impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS V_I (V)	TEST CONDITIONS I_O (mA)	V_{CC} (V)	25°C MIN	25°C TYP	25°C MAX	-40°C TO 85°C MIN	-40°C TO 85°C MAX	-55°C TO 125°C MIN	-55°C TO 125°C MAX	UNITS
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-6	4.5	-	-	0.26	-	0.33	-	0.4	V
			-7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC} (Note 3)	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	V_O = V_{CC} or GND	5.5	-	-	±0.5	-	±5	-	±10	µA

NOTE:

3. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
$1I_O$ - $1I_3$, $2I_O$-$2I_3$	0.4
$1E_O$, $2E_O$, S_0, S_1	1

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Table, e.g., 360µA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay Select to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	175	-	220	-	265	ns
			4.5	-	-	35	-	44	-	53	ns
		C_L =15pF	5	-	14	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	30	-	37	-	45	ns

Switching Specifications Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Data to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	175	-	220	-	265	ns
			4.5	-	-	35	-	44	-	53	ns
		C_L =15pF	5	-	14	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	30	-	37	-	45	ns
Disable Delay Times	t_{PHZ}, t_{PLZ}	C_L = 50pF	2	-	-	150	-	190	-	225	ns
		C_L = 50pF	4.5	-	-	30	-	38	-	45	ns
		CL = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	26	-	33	-	38	ns
Enable Delay Times	t_{PZH}, t_{PZL}	C_L = 50pF	2	-	-	110	-	140	-	165	ns
		CL = 50pF	4.5	-	-	22	-	28	-	33	ns
		CL = 15pF	5	-	9	-	-	-	-	-	ns
		CL = 50pF	6	-	-	19	-	24	-	28	ns
Output Transition Times	t_{TLH}, t_{THL}	C_L = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C_I	-	-	-	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5	-	46	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay Select to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	40	-	50	-	60	ns
		C_L =15pF	5	-	16	-	-		-	-	ns
Data to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	38	-	48	-	57	ns
		C_L =15pF	5	-	16	-	-	-	-	-	ns
Disable Delay Times	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-		30	-	38	-	45	ns
		C_L =15pF	5	-	12	-	-	-	-	-	ns
Enable Delay Times	t_{PZH}, t_{PZL}	C_L = 50pF	4.5	-	-	30	-	38	-	45	ns
		C_L =15pF	5	-	12	-	-	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	C_{IN}	-	-	-	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5)	C_{PD}	-	5	-	52	-	-	-	-	-	pF

NOTES:

4. C_{PD} is used to determine the dynamic power consumption, per multiplexer.
5. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

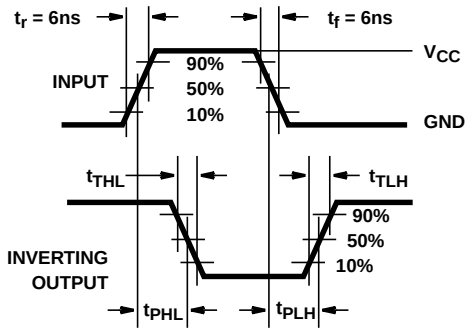


FIGURE 1. HC AND HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

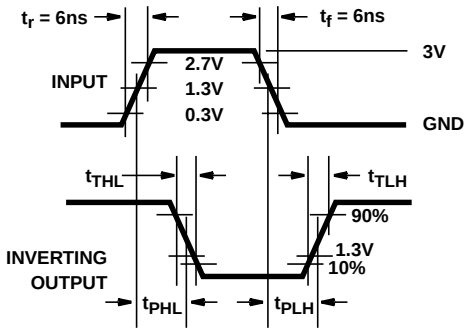


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

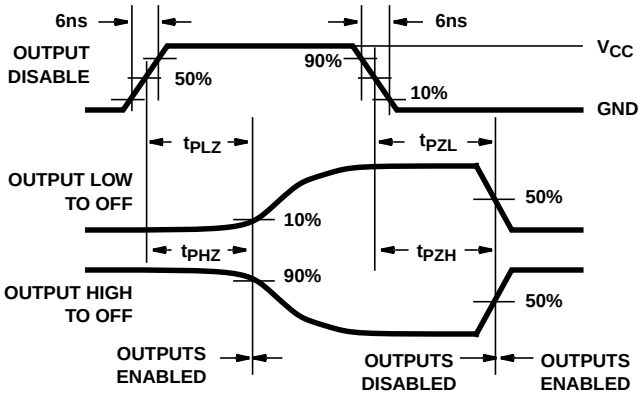


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

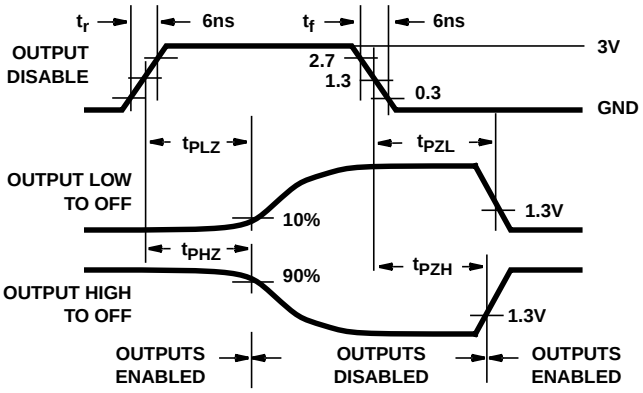
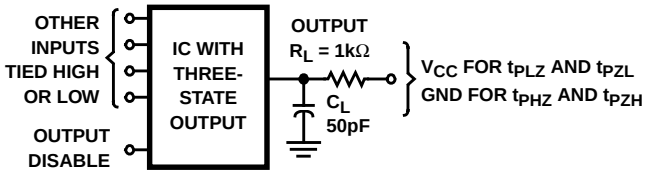


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CD74HC253E	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC253E	Samples
CD74HC253M	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC253M	Samples
CD74HC253MT	ACTIVE	SOIC	D	16	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC253M	Samples
CD74HCT253E	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT253E	Samples
CD74HCT253EE4	ACTIVE	PDIP	N	16	25	TBD	Call TI	Call TI	-55 to 125		Samples
CD74HCT253M	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT253M	Samples
CD74HCT253M96	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT253M	Samples
CD74HCT253MG4	ACTIVE	SOIC	D	16	40	TBD	Call TI	Call TI	-55 to 125		Samples
CD74HCT253MT	ACTIVE	SOIC	D	16	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT253M	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

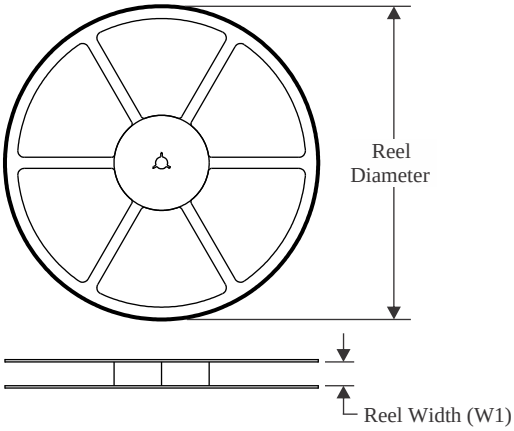
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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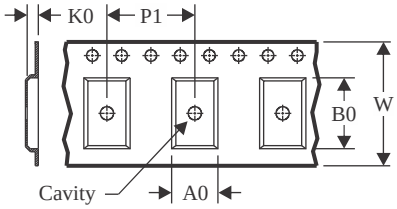
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TAPE AND REEL INFORMATION

REEL DIMENSIONS

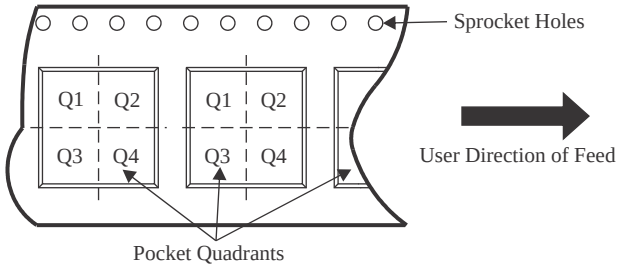


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

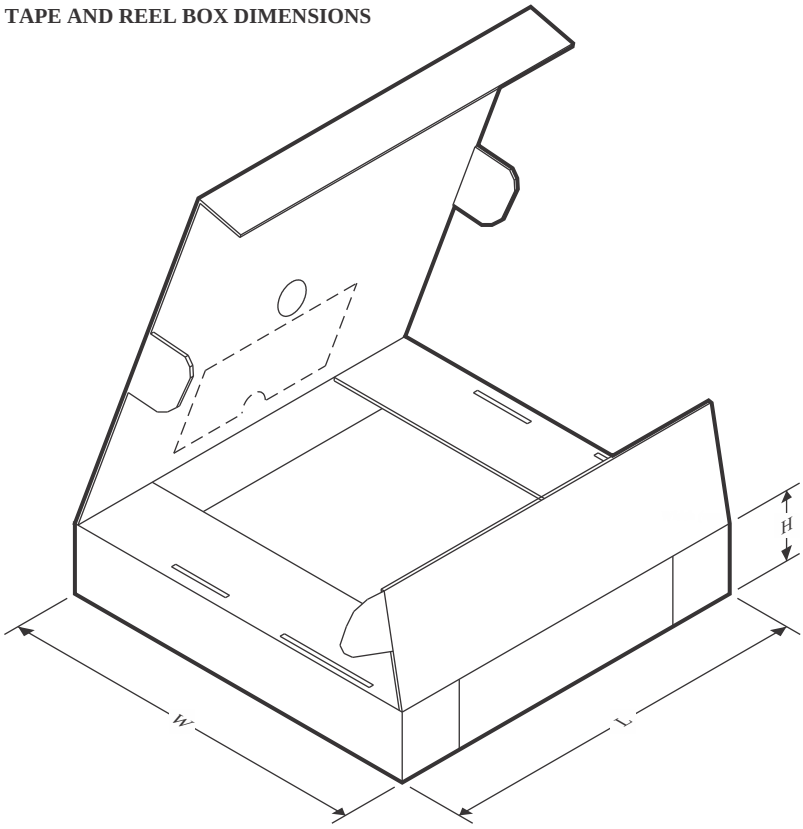
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HCT253M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1

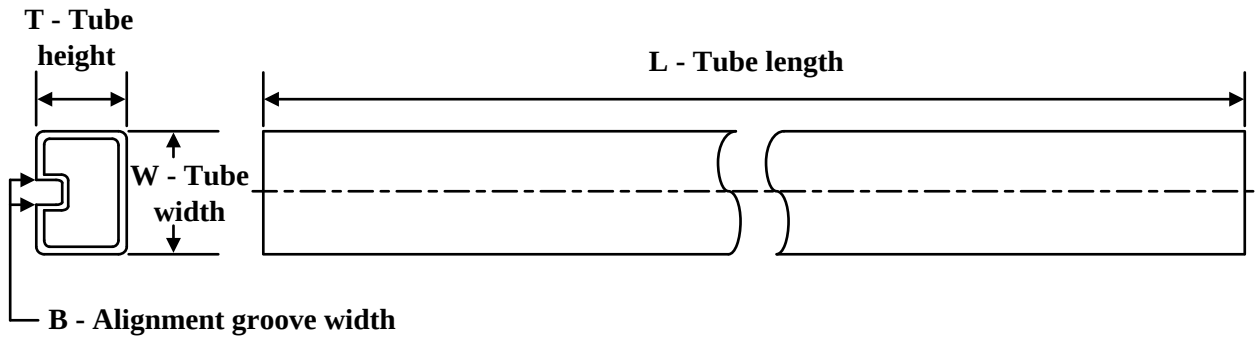
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HCT253M96	SOIC	D	16	2500	340.5	336.1	32.0

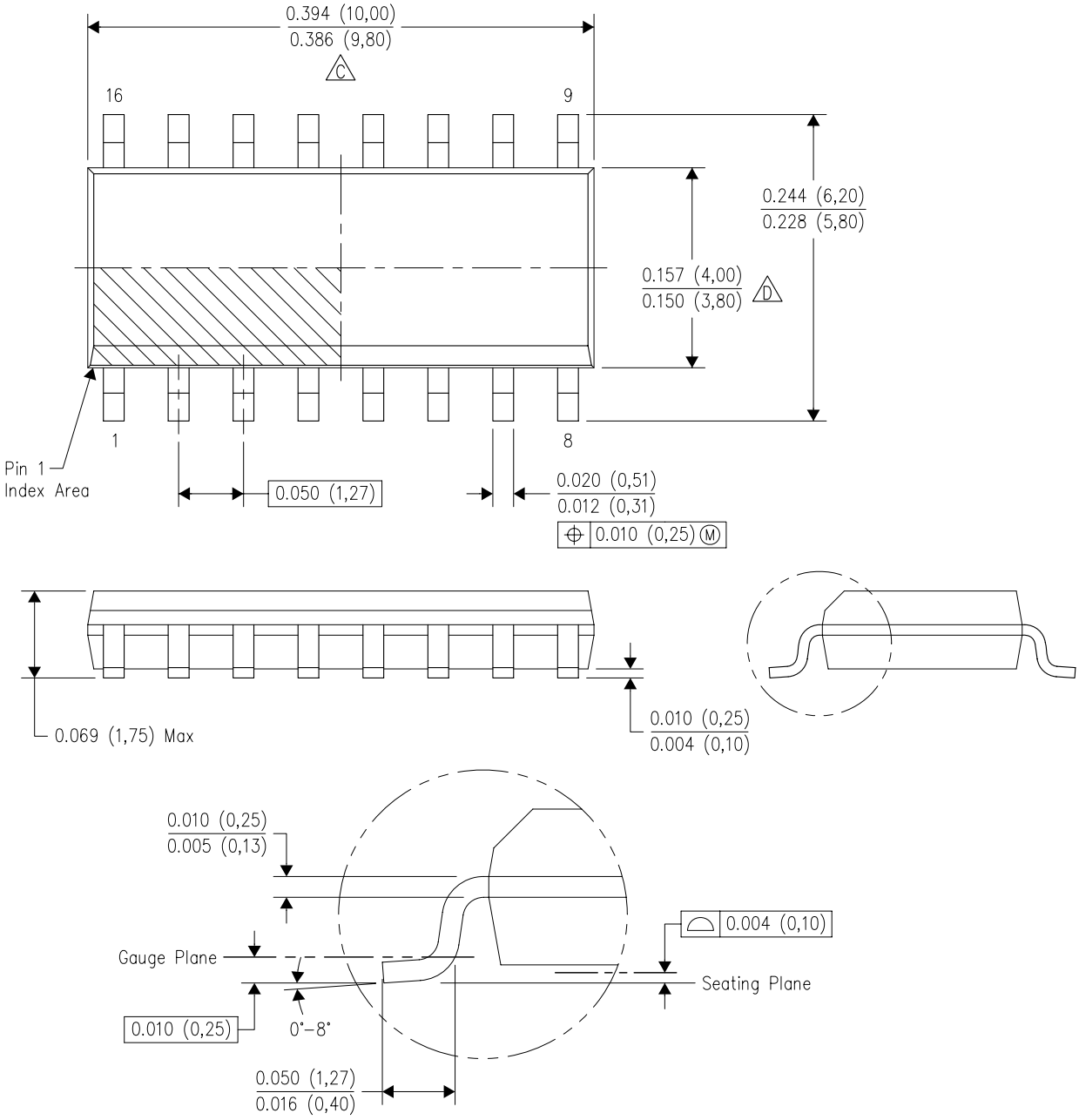
TUBE



*All dimensions are nominal

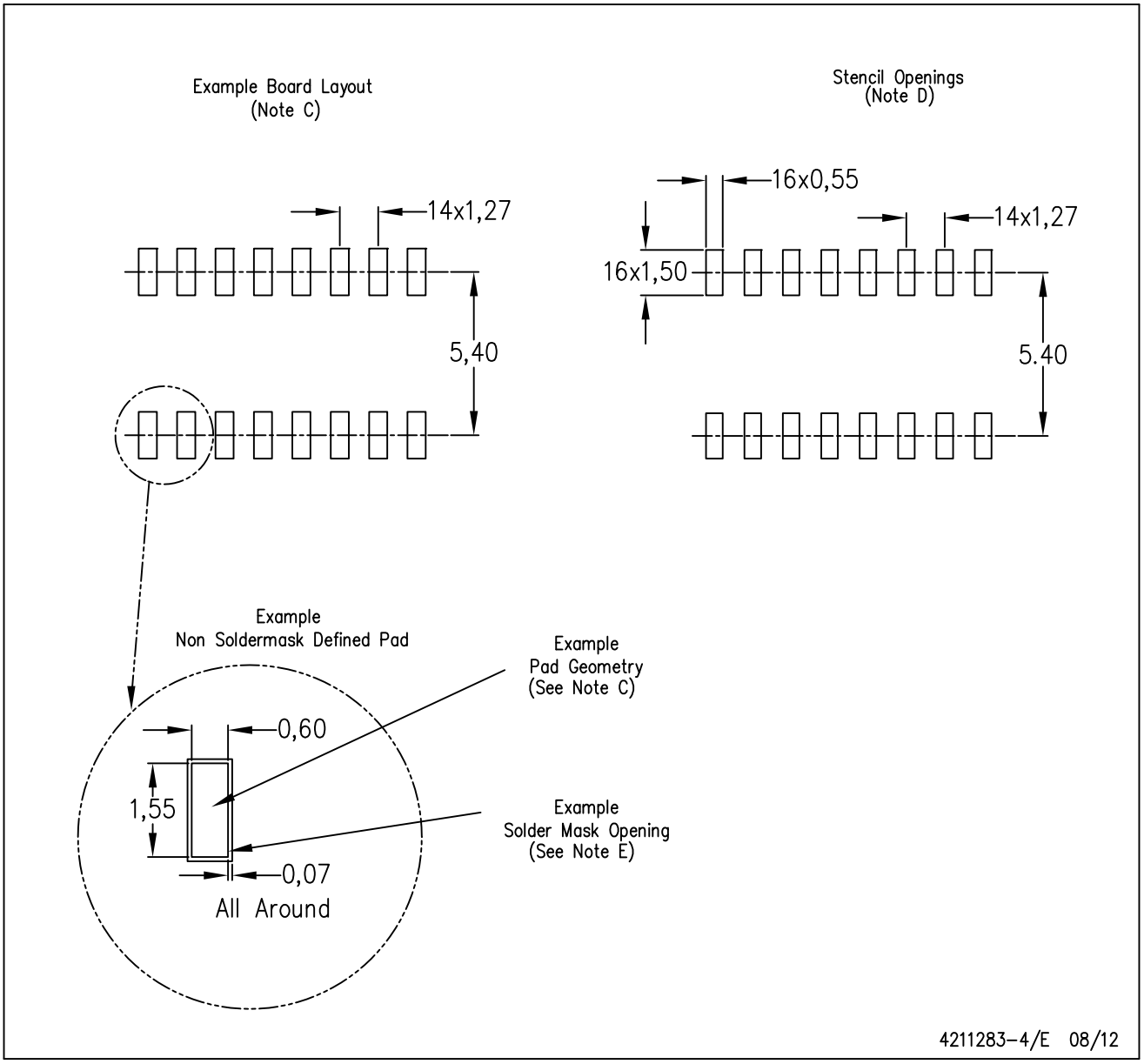
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CD74HC253E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC253E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC253M	D	SOIC	16	40	507	8	3940	4.32
CD74HCT253E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT253E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT253M	D	SOIC	16	40	507	8	3940	4.32

D (R–PDSO–G16) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AC.

D (R–PDSO–G16) PLASTIC SMALL OUTLINE

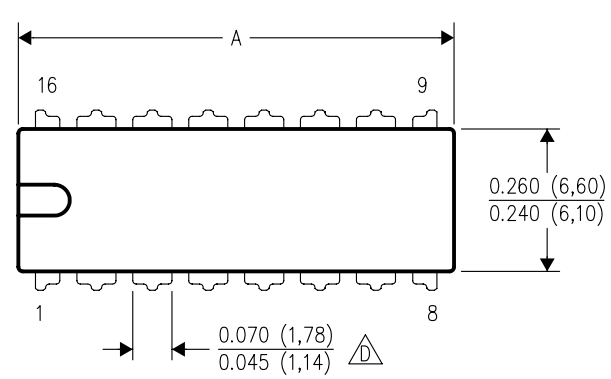


NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

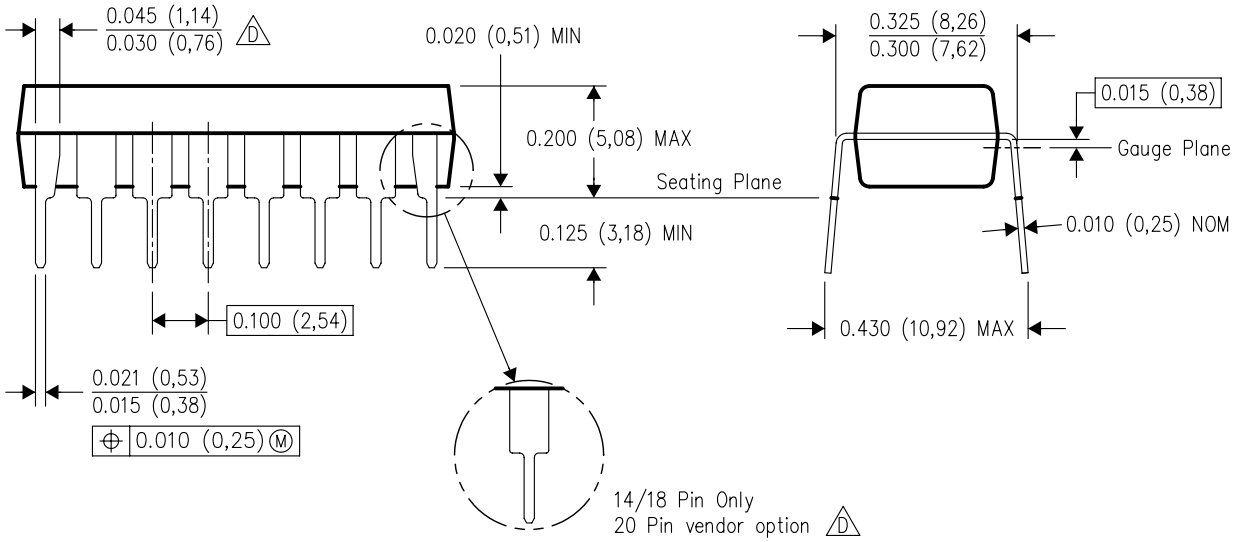
N (R–PDIP–T**)

PLASTIC DUAL–IN–LINE PACKAGE

16 PINS SHOWN



DIM \ PINS **	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS–001 VARIATION (C)	AA	BB	AC	AD



4040049/E 12/2002

NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS–001, except 18 and 20 pin minimum body length (Dim A).
D. The 20 pin end lead shoulder width is a vendor option, either half or full width.

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